NSN 5961-01-210-8901

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View Online at https://aerobasegroup.com/nsn/5961-01-210-8901 **Inclosure Material:** Metal **Overall Length:** 0.260 inches **Terminal Length:** 1.500 inches **Overall Diameter:** 0.335 inches **Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-5 **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method: Terminal Terminal Circle Diameter:** 0.200 inches **Features Provided:** Hermetically sealed case and quality assurance level txv **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 2.2 forward voltage, peak **Current Rating Per Characteristic:** 2.00 milliamperes forward current, total rms peak **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pnpn **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 3 uninsulated wire lead **Specification Data:** 81349-mil-s-19500/276 government specification Shelf Life: N/a **Unit Of Measure:**

No

Demilitarization:

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